30.0A 100V Schottky Barrier Diode

Productor Character

- Multilayer Metal -Silicon Potential Structure.
- Low Leakage Current.
- High Current Capability, High Efficiency.
- High Junction Temperature Capability.
- RoHs Product.

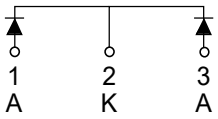
Primary Use

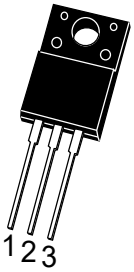
- Low Voltage High Frequency Switching Power Supply.
- Low Voltage High Frequency Invers Circuit.
- Low Voltage Continued Circuit and Protection Circuit.

Summarize

- EBR30L100FCT Device optimized for ultra-low forward voltage drop to maximize efficiency in Power Supply applications.

Equivalent Circuit





Package:ITO-220AB

EBR30L100FCT

EBR30L100FCT-HF

HF=Halogen Free

Absolute Maximum Ratings

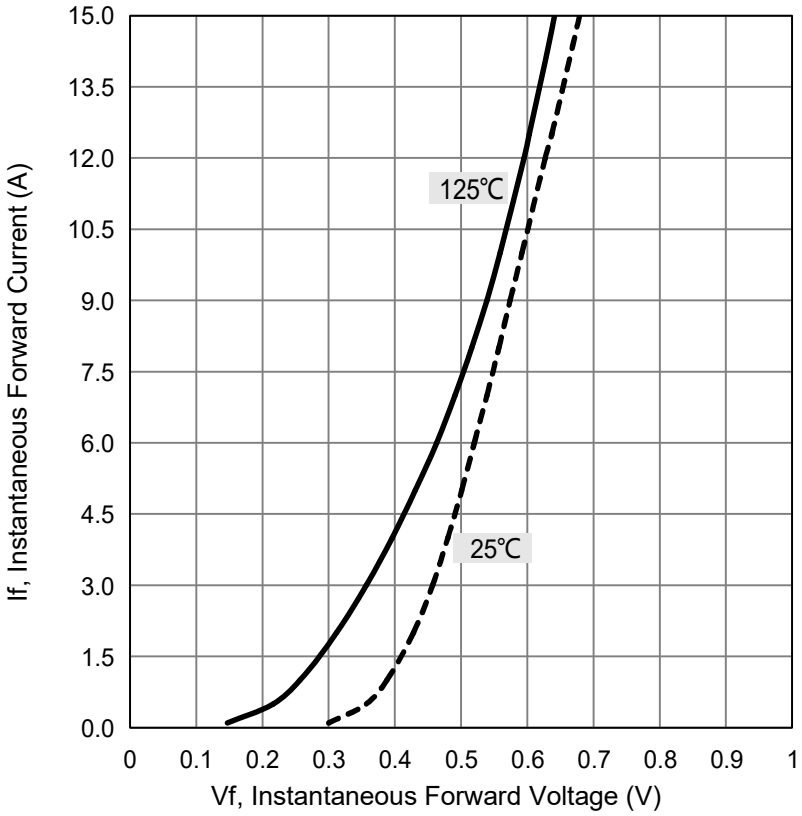
Item		Symbol	Data	Unit
Maximal Inverted Repetitive Peak Voltage		V_{RRM}	100	V
Average Rectified Forward Current(Rated VR-20Khz Square Wave)-50% duty cycle	Per Device	I_{FAV}	30	A
	Per Diode		15	
Forward Peak Surge Current(Rated Load 8.3 Half Mssine Wave-According to JEDEC Method)	Per Diode	I_{FSM}	250	A
Operating Junction Temperature		T_J	-40～150	℃
Storage Temperature		T_{STG}	-40～150	℃
Typical Thermal Resistance(per leg)	Package=ITO-220AB	$R_{\theta JC}$	4	℃/W

Electricity Characteristics

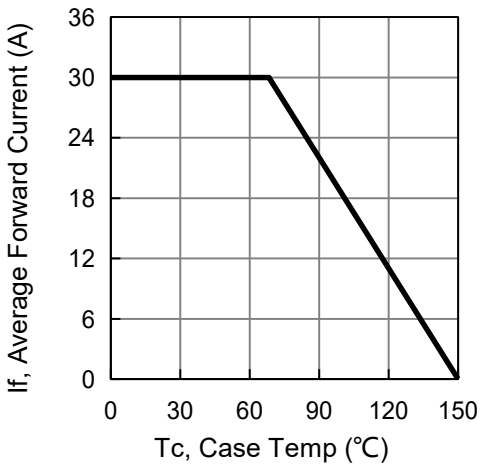
Item	Test Condition		Value(min)	Value(typ)	Value(max)	Unit
V_B	TJ =25℃	IR=1mA	100	—	—	V
I_R	TJ =25℃	VR=100V	—	—	0.03	mA
	TJ =125℃	VR=100V	—	—	15.00	mA
V_F	TJ =25℃	IF=15A	—	0.68	0.75	V
	TJ =125℃	IF=15A	—	—	0.7	V

Characteristic Curves

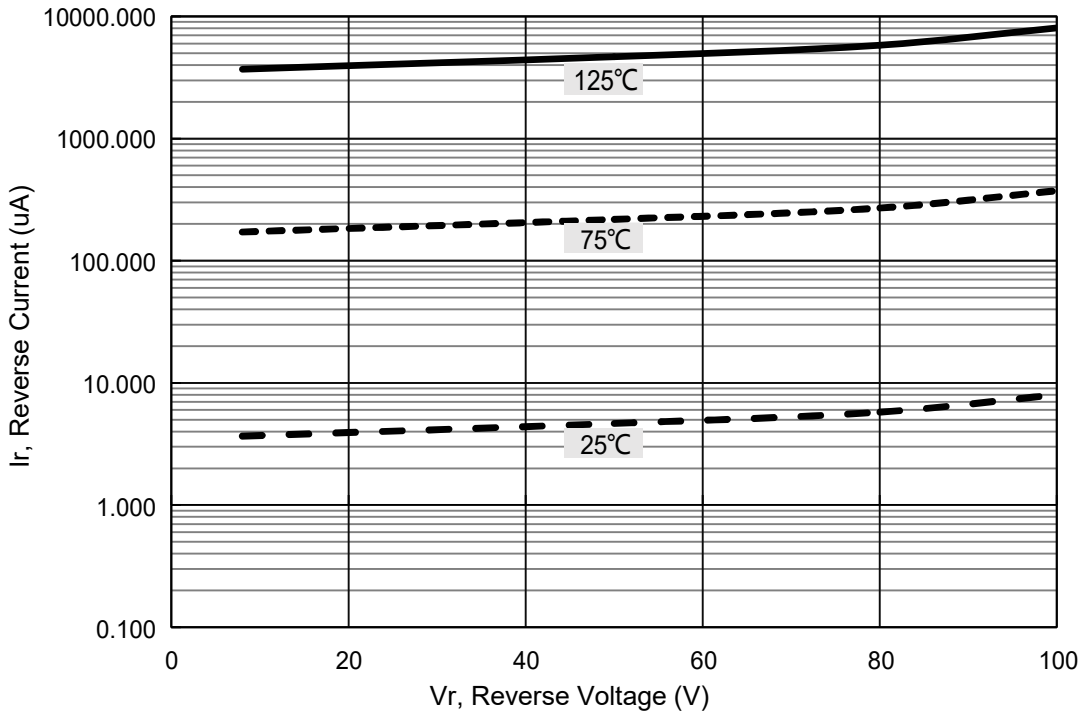
The forward voltage and forward current curve



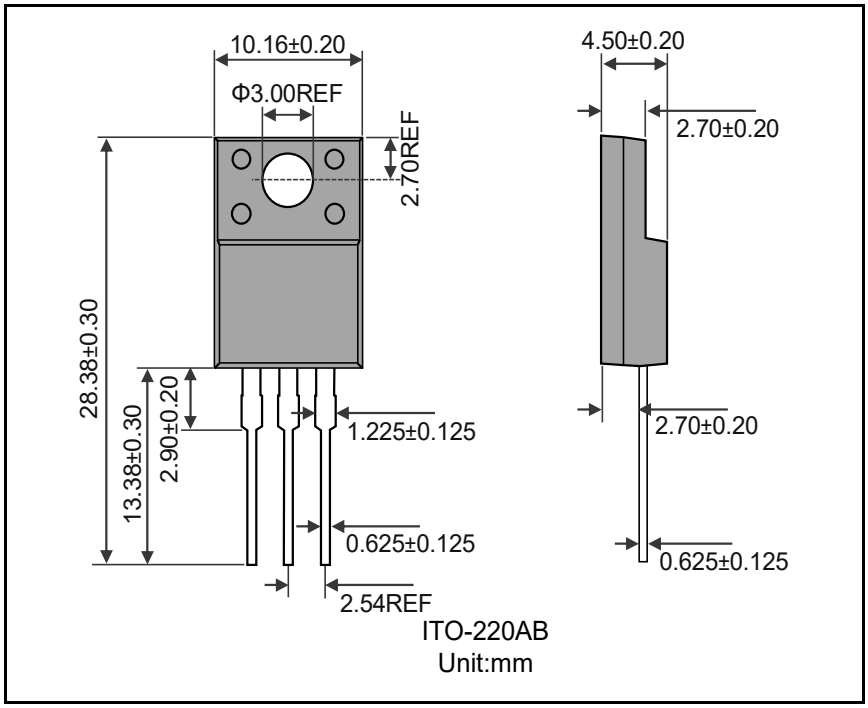
Current derating curve, perelement



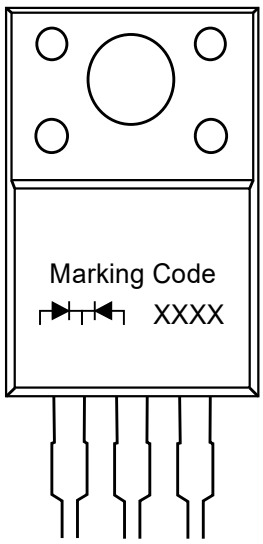
The reverse leak current and the reverse voltage (single-device) curve.



Package Outline Dimensions



Marking Information



"Marking Code"= The Following
"XXXX"= Date Code Marking

Marking Code	Part Number
EBR30L100F	EBR30L100FCT
	EBR30L100FCT-HF

Packing Information

Packaging	Part Number	Quantity(pcs)	Size(mm)
Tube	Tube	50	L534×W33×H7
	Inner Box	1000	L560×W150×H40
	Outer Box	5000	L570×W235×H175